N–Channel JFETs

J108 **SST108**
J109 **SST109**
J110 **SST110**

PRODUCT SUMMARY				
Part Number	**$V_{GS(off)}$ (V)**	**$r_{DS(on)}$ Max (Ω)**	**$I_{D(off)}$ Typ (pA)**	**t_{ON} Typ (ns)**
J/SST108	–3 to –10	8	20	4
J/SST109	–2 to –6	12	20	4
J/SST110	–0.5 to –4	18	20	4

FEATURES

- Low On-Resistance: J108 <8 Ω
- Fast Switching—t_{ON}: 4 ns
- Low Leakage: 20 pA
- Low Capacitance: 11 pF
- Low Insertion Loss

BENEFITS

- Low Error Voltage
- High-Speed Analog Circuit Performance
- Negligible “Off-Error” Excellent Accuracy
- Good Frequency Response
- Eliminates Additional Buffering

APPLICATIONS

- Analog Switches
- Choppers
- Sample-and-Hold
- Normally “On” Switches
- Current Limiters

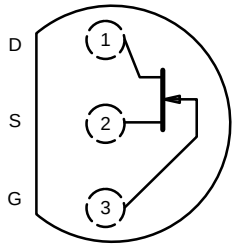
DESCRIPTION

The J/SST108 series is designed with high-performance analog switching applications in mind. It features low on-resistance, good off-isolation, and fast switching.

The SST108 series is comprised of surface-mount devices featuring the lowest $r_{DS(on)}$ of any TO-236 (SOT-23) JFET device.

The TO-226AA (TO-92) plastic package provides a low-cost option. Both the J and SST series are available in tape-and-reel for automated assembly (see Packaging Information). For similar products packaged in TO-206AC (TO-52), see the 2N5432/5433/5434 data sheet.

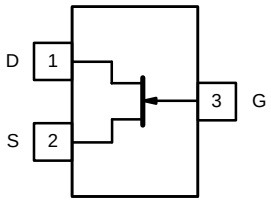
TO-226AA
(TO-92)



Top View

J108, J109, J110

TO-236
(SOT-23)



Top View

SST108 (I8)*
SST109 (I9)*
SST110 (I0)*

*Marking Code for TO-236

ABSOLUTE MAXIMUM RATINGS

Gate-Drain, Gate-Source Voltage . . . . . –25 V
Gate Current . . . . . 50 mA
Lead Temperature ($^1/_{16}$" from case for 10 sec.) . . . . . 300°C
Storage Temperature . . . . . –55 to 150°C
Operating Junction Temperature . . . . . –55 to 150°C
Power Dissipation[a] . . . . . 350 mW

Notes
a. Derate 2.8 mW/°C above 25°C

SPECIFICATIONS (T_A = 25°C UNLESS OTHERWISE NOTED)

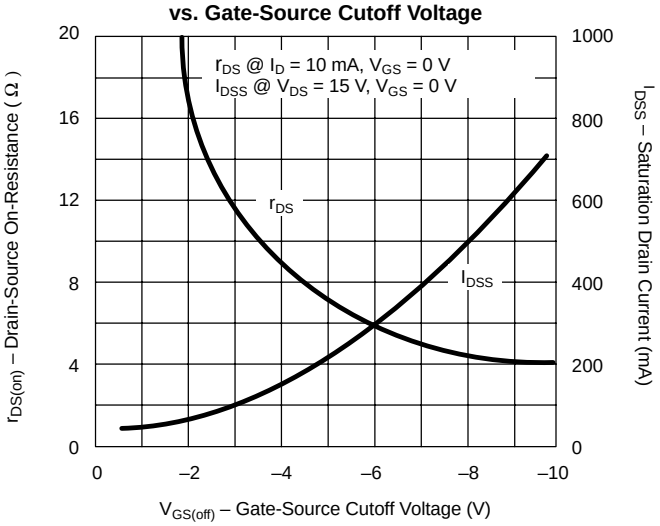
Parameter	Symbol	Test Conditions	Typ[a]	Limits J/SST108 Min	J/SST108 Max	J/SST109 Min	J/SST109 Max	J/SST110 Min	J/SST110 Max	Unit
Static										
Gate-Source Breakdown Voltage	$V_{(BR)GSS}$	I_G = –1 µA , V_{DS} = 0 V	–32	–25		–25		–25		V
Gate-Source Cutoff Voltage	$V_{GS(off)}$	V_{DS} = 5 V, I_D = 1 µA		–3	–10	–2	–6	–0.5	–4	
Saturation Drain Current[b]	I_{DSS}	V_{DS} = 15 V, V_{GS} = 0 V		80		40		10		mA
Gate Reverse Current	I_{GSS}	V_{GS} = –15 V, V_{DS} = 0 V	–0.01		–3		–3		–3	nA
		T_A = 125°C	–5							
Gate Operating Current	I_G	V_{DG} = 10 V, I_D = 10 mA	–0.01							
Drain Cutoff Current	$I_{D(off)}$	V_{DS} = 5 V, V_{GS} = –10 V	0.02		3		3		3	
		T_A = 125°C	1.0							
Drain-Source On-Resistance	$r_{DS(on)}$	V_{GS} = 0 V, V_{DS} ≤ 0.1 V			8		12		18	Ω
Gate-Source Forward Voltage	$V_{GS(F)}$	I_G = 1 mA , V_{DS} = 0 V	0.7							V
Dynamic										
Common-Source Forward Transconductance	g_{fs}	V_{DS} = 5 V, I_D = 10 mA, f = 1 kHz	17							mS
Common-Source Output Conductance	g_{os}		0.6							
Drain-Source On-Resistance	$r_{ds(on)}$	V_{GS} = 0 V, I_D = 0 mA , f = 1 kHz			8		12		18	Ω
Common-Source Input Capacitance	C_{iss}	V_{DS} = 0 V, V_{GS} = 0 V, f = 1 MHz — SST	60							pF
		J Series	60		85		85		85	
Common-Source Reverse Transfer Capacitance	C_{rss}	V_{DS} = 0 V, V_{GS} = –10 V, f = 1 MHz — SST	11							
		J Series	11		15		15		15	
Equivalent Input Noise Voltage	$\overline{e}_n$	V_{DG} = 5 V, I_D = 10 mA, f = 1 kHz	3.5							$\frac{nV}{\sqrt{Hz}}$
Switching										
Turn-On Time	$t_{d(on)}$	V_{DD} = 1.5 V, $V_{GS(H)}$ = 0 V, See Switching Diagram	3							ns
	t_r		1							
Turn-Off Time	$t_{d(off)}$		4							
	t_f		18							

Notes
a. Typical values are for DESIGN AID ONLY, not guaranteed nor subject to production testing.
b. Pulse test: PW ≤300 µs duty cycle ≤3%.

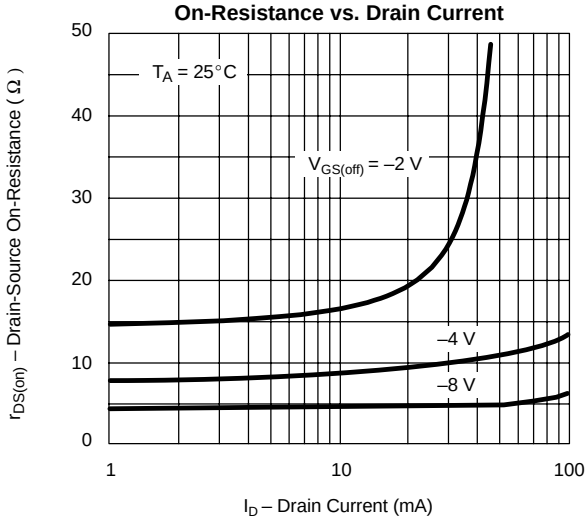
NIP

TYPICAL CHARACTERISTICS (T_A = 25°C UNLESS OTHERWISE NOTED)

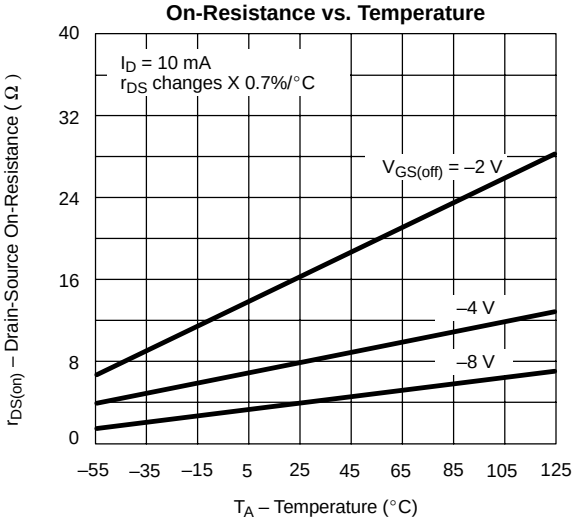
On-Resistance and Drain Current vs. Gate-Source Cutoff Voltage



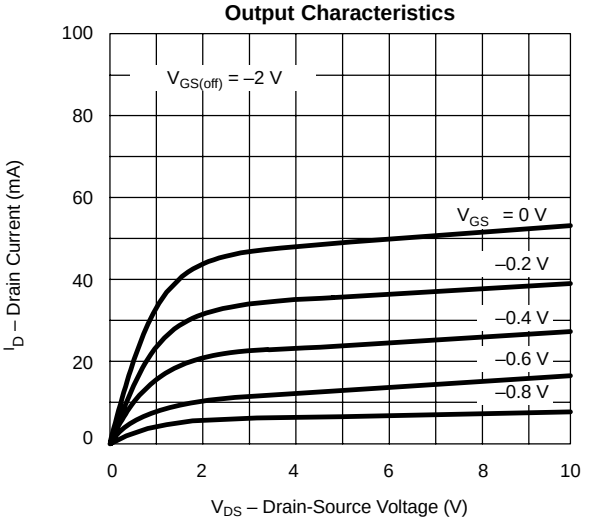
On-Resistance vs. Drain Current



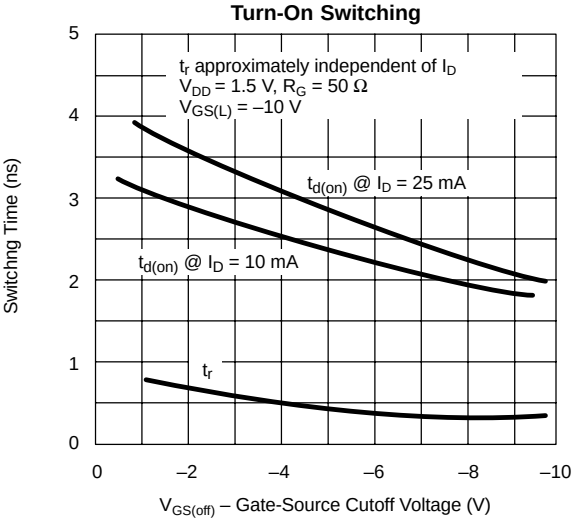
On-Resistance vs. Temperature



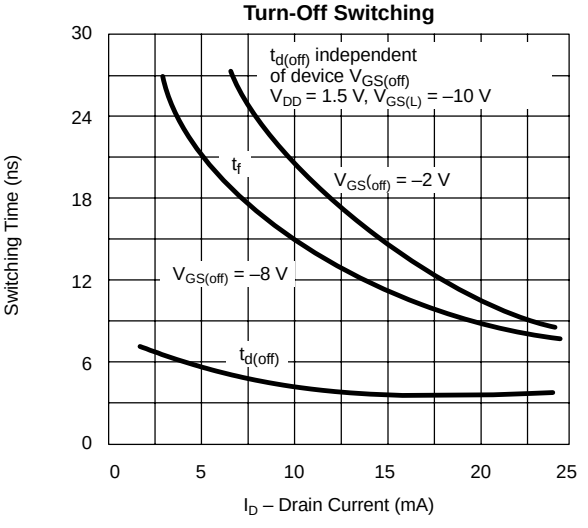
Output Characteristics



Turn-On Switching

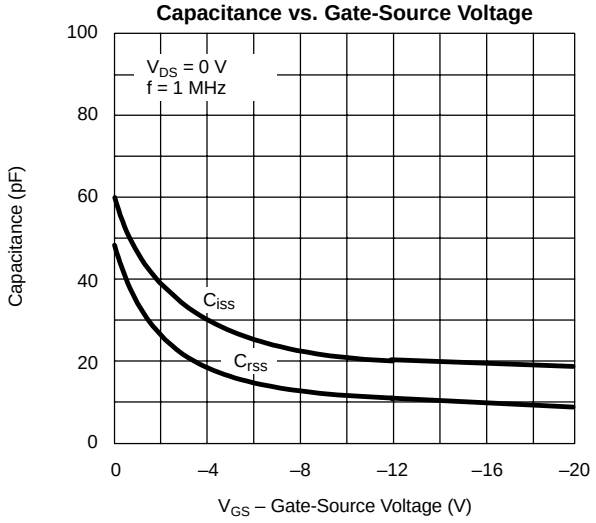


Turn-Off Switching

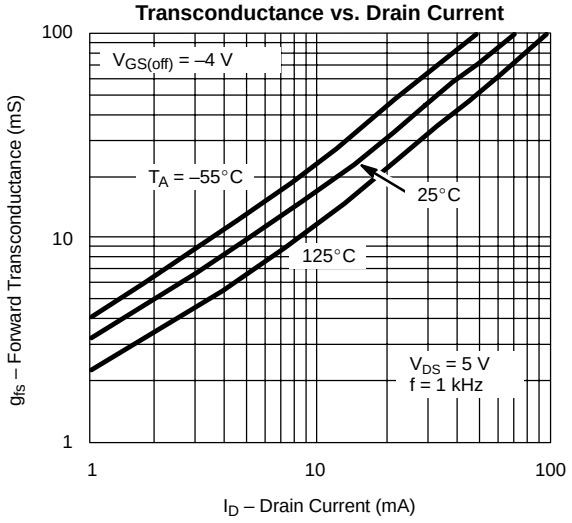


TYPICAL CHARACTERISTICS (T_A = 25°C UNLESS OTHERWISE NOTED)

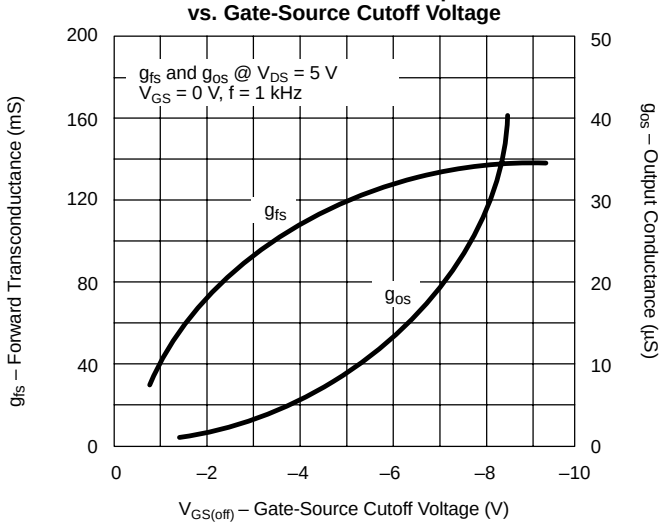
Capacitance vs. Gate-Source Voltage



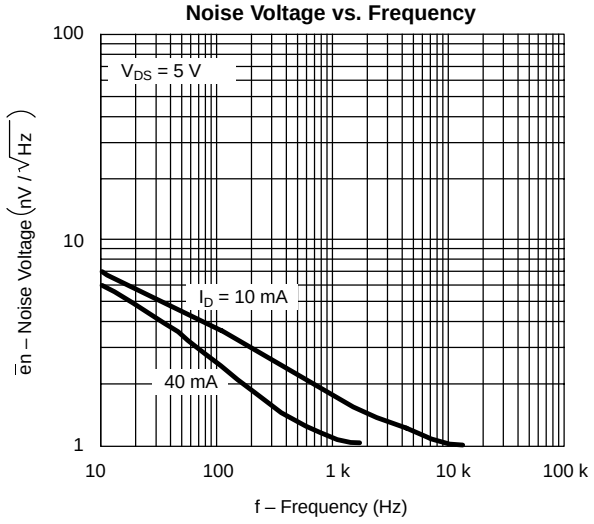
Transconductance vs. Drain Current



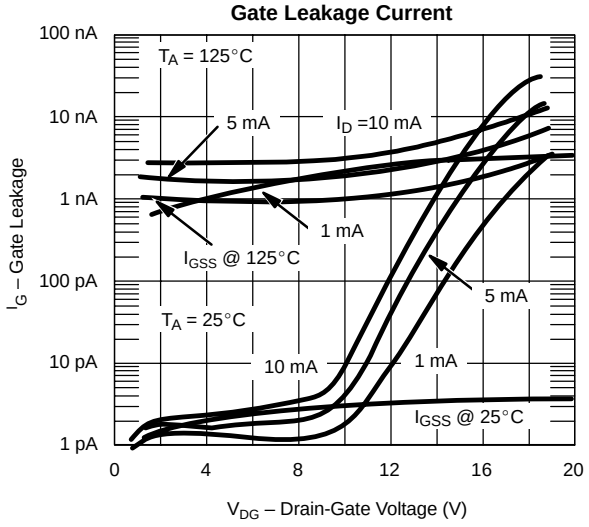
Forward Transconductance and Output Conductance vs. Gate-Source Cutoff Voltage



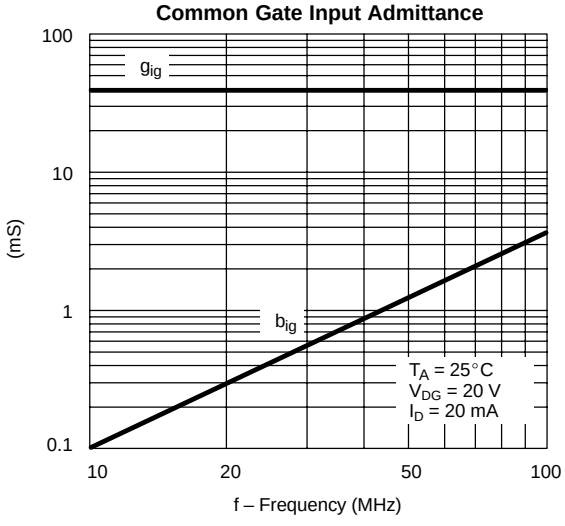
Noise Voltage vs. Frequency



Gate Leakage Current

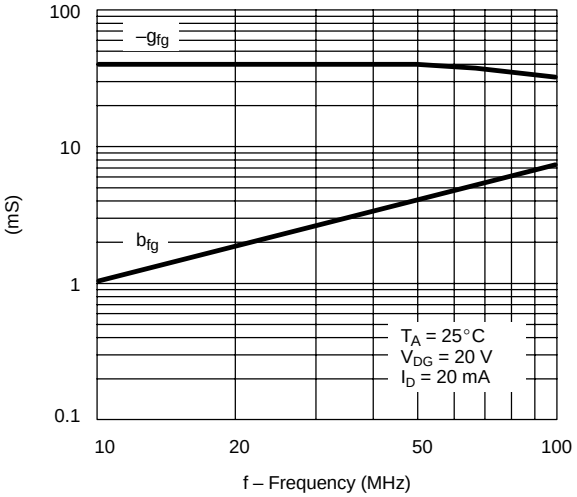


Common Gate Input Admittance

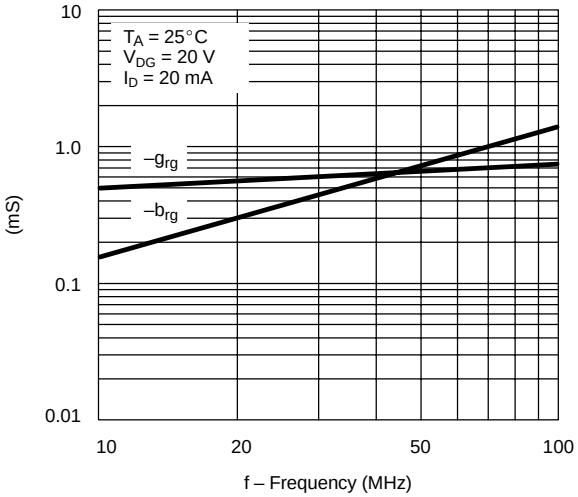


TYPICAL CHARACTERISTICS (T_A = 25°C UNLESS OTHERWISE NOTED)

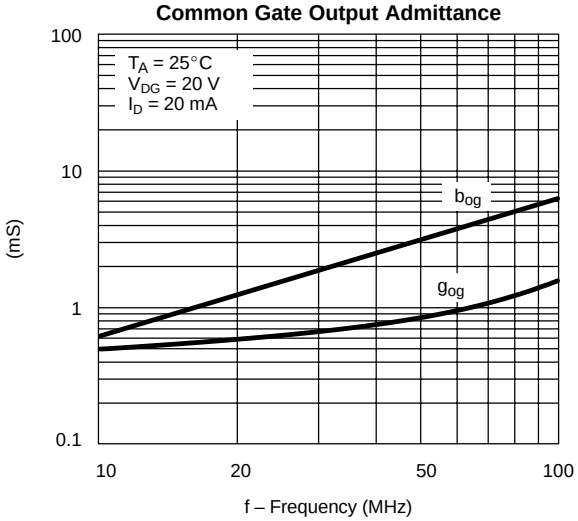
Common Gate Forward Admittance



Common Gate Reverse Admittance



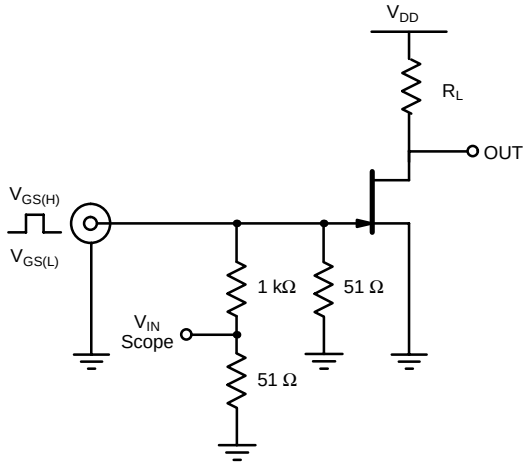
Common Gate Output Admittance



SWITCHING TIME TEST CIRCUIT

	J/SST108	J/SST109	J/SST110
$V_{GS(L)}$	–12 V	–7 V	–5 V
R_L*	150 Ω	150 Ω	150 Ω
$I_{D(on)}$	10 mA	10 mA	10 mA

*Non-inductive



INPUT PULSE

Rise Time < 1 ns
Fall Time < 1 ns
Pulse Width 100 ns
PRF 1 MHz

SAMPLING SCOPE

Rise Time 0.4 ns
Input Resistance 10 MΩ
Input Capacitance 1.5 pF